

Features

- Reduced RFI and EMI
- Reduced Snubbing
- Extensive Characterization of Recovery Parameters
- Hermetic

$V_R = 200V$

$I_{F(AV)} = 35A$

$t_{fr} = 35ns$

Description

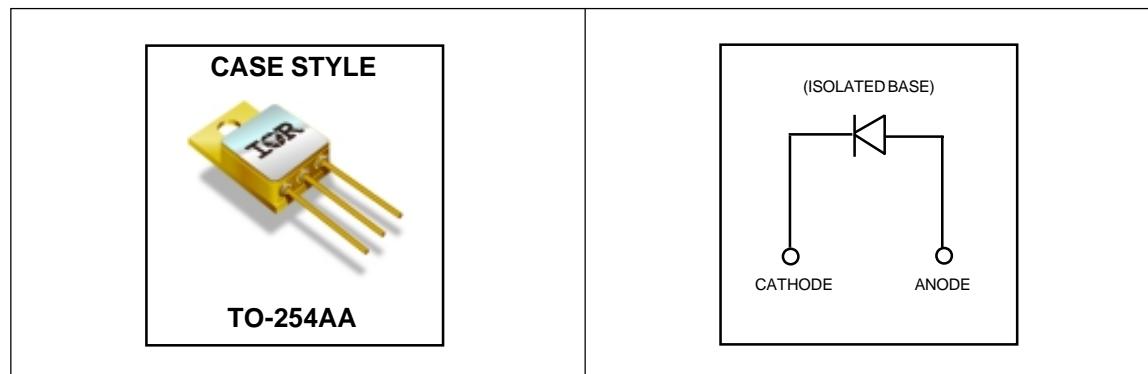
HEXFRED™ diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_R	Cathode to Anode Voltage	200	V
$I_{F(AV)}$	Continuous Forward Current, ① $T_C = 80^\circ C$	35	A
I_{FSM}	Single Pulse Forward Current, ② $T_C = 25^\circ C$	150	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	125	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

Note: ① D.C. = 50% rect. wave

② 1/2 sine wave, 60 Hz , P.W. = 8.33 ms



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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V_{BR}	Cathode Anode Breakdown Voltage	200	—	—	V	$I_R = 100\mu\text{A}$
V_F	Forward Voltage See Fig. 1	—	—	1.25	V	$I_F = 20\text{A}, T_J = -55^\circ\text{C}$
		—	—	1.15		$I_F = 20\text{A}, T_J = 25^\circ\text{C}$
		—	—	1.41		$I_F = 35\text{A}, T_J = 25^\circ\text{C}$
		—	—	1.92		$I_F = 70\text{A}, T_J = 25^\circ\text{C}$
		—	—	1.01		$I_F = 20\text{A}, T_J = 125^\circ\text{C}$
I_R	Reverse Leakage Current See Fig. 2	—	—	10	μA	$V_R = V_R \text{ Rated}$
		—	—	1.0	mA	$V_R = V_R \text{ Rated}, T_J = 125^\circ\text{C}$
C_T	Junction Capacitance, See Fig. 3	—	—	175	pF	$V_R = 200\text{V}$
L_S	Series Inductance	—	7.8	—	nH	Measured from anode lead to cathode lead, 6mm (0.025 in) from package

Dynamic Recovery Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
t_{rr}	Reverse Recovery Time	—	—	35	ns	$I_F = 1.0\text{A}, V_R = 30\text{V}, di/dt = 200\text{A}/\mu\text{s}$
t_{rr1}	Reverse Recovery Time	—	45	—	ns	$T_J = 25^\circ\text{C}$ See Fig. 5
t_{rr2}		—	68	—		
I_{RRM1}	Peak Recovery Current	—	3.3	—	A	$T_J = 25^\circ\text{C}$ See Fig. 6
I_{RRM2}		—	7.6	—		
Q_{rr1}	Reverse Recovery Charge	—	76	—	nC	$T_J = 25^\circ\text{C}$ See Fig. 7
Q_{rr2}		—	270	—		
$di_{(rec)M}/dt_1$	Peak Rate of Fall of Recovery Current During t_b	—	236	—	A/ μs	$T_J = 25^\circ\text{C}$ See Fig. 8
$di_{(rec)M}/dt_2$		—	1020	—		

Thermal - Mechanical Characteristics

	Parameter	Typ.	Max.	Units
R_{thJC}	Junction-to-Case	—	1.0	°C/W
Wt	Weight	9.3	—	g

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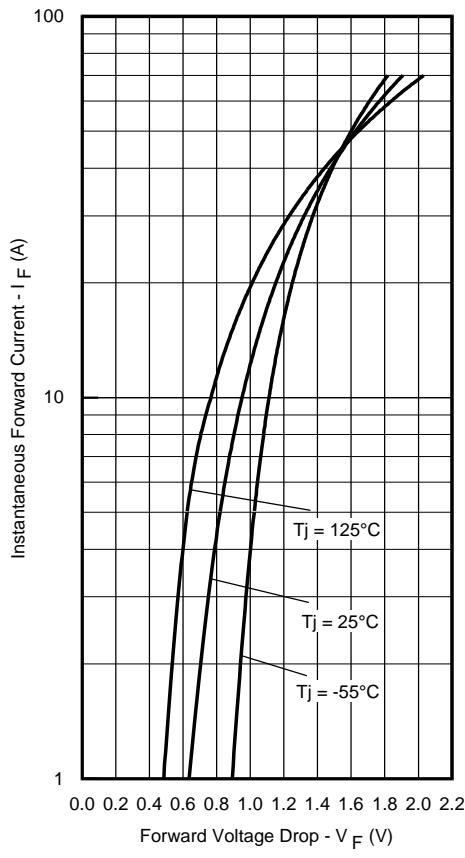


Fig. 1 - Maximum Forward Voltage Drop Vs.
Instantaneous Forward Current

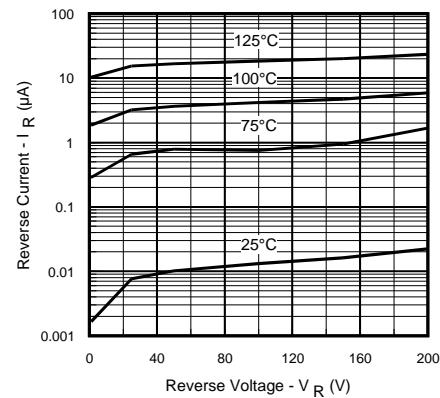


Fig. 2 - Typical Reverse Current Vs. Reverse Voltage

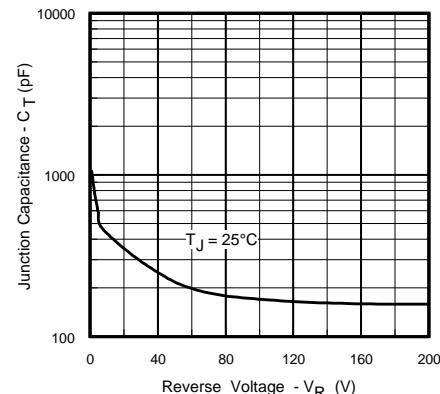


Fig. 3 - Typical Junction Capacitance Vs.
Reverse Voltage

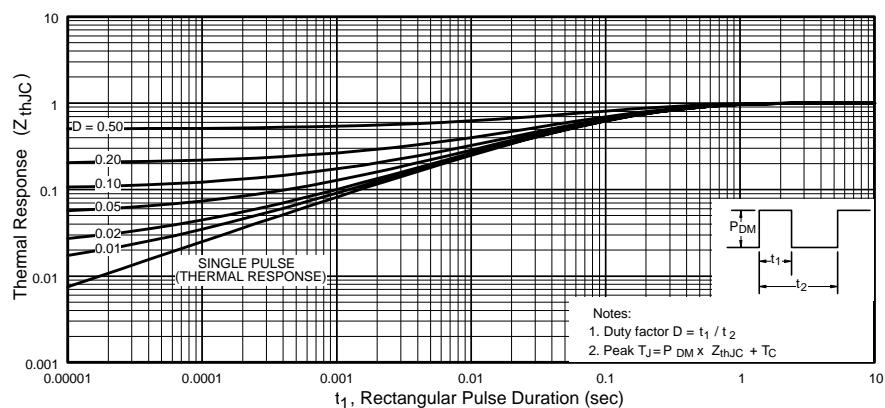


Fig. 4 - Maximum Thermal Impedance Z_{thjc} Characteristics

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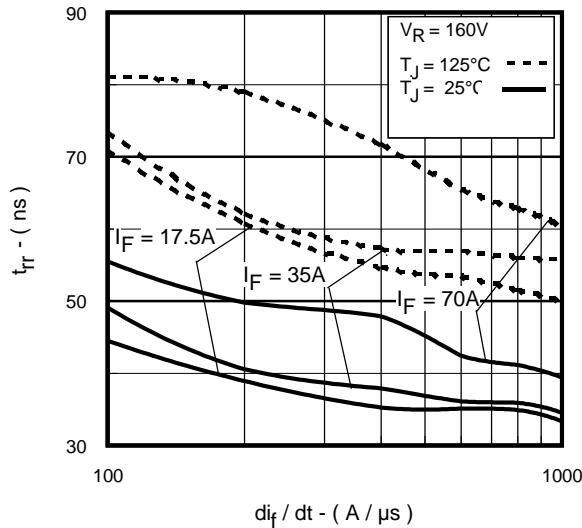


Fig. 5 - Typical Reverse Recovery Vs. di_f/dt ,

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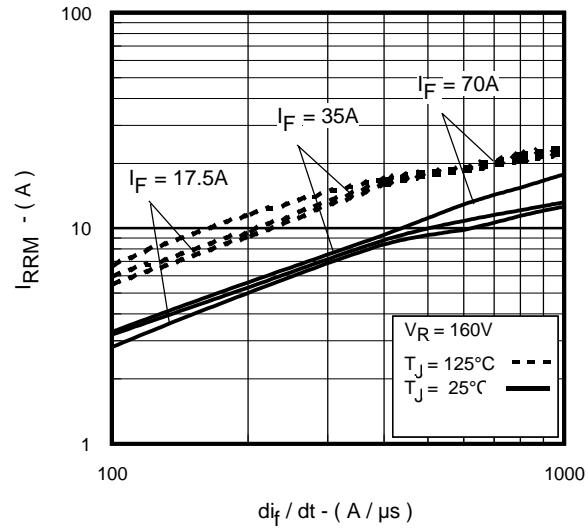


Fig. 6 - Typical Recovery Current Vs. di_f/dt ,

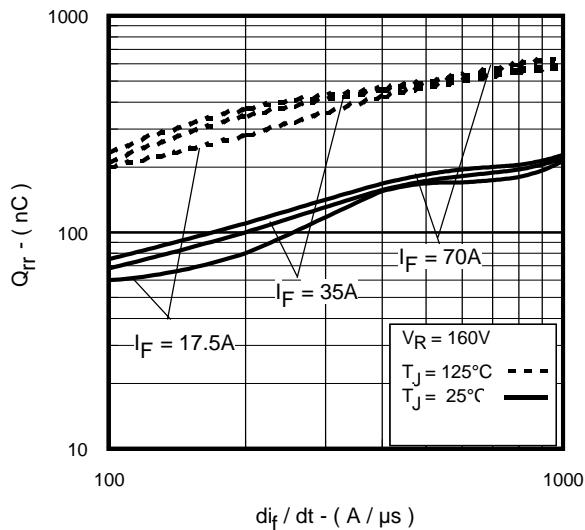


Fig. 7 - Typical Stored Charge Vs. di_f/dt

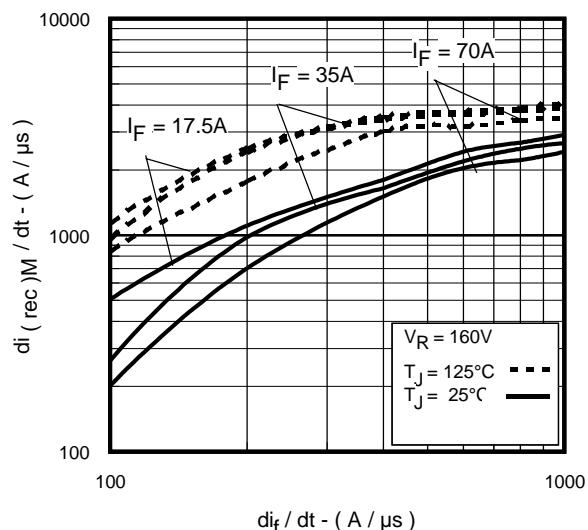


Fig. 8 - Typical $di_{(rec)}/dt$ Vs. di_f/dt

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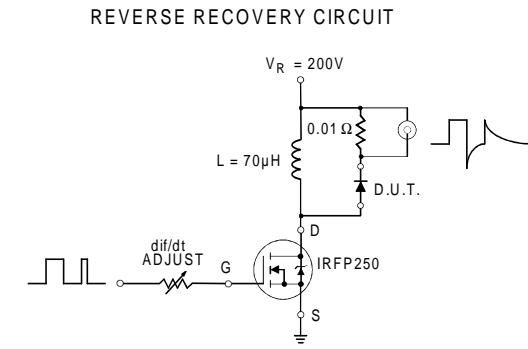


Fig. 9 - Reverse Recovery Parameter Test Circuit

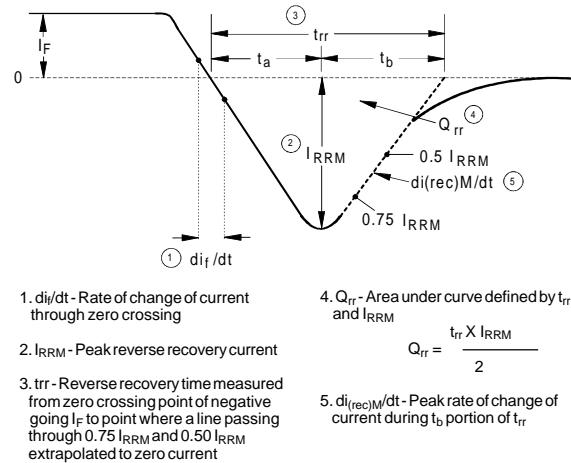
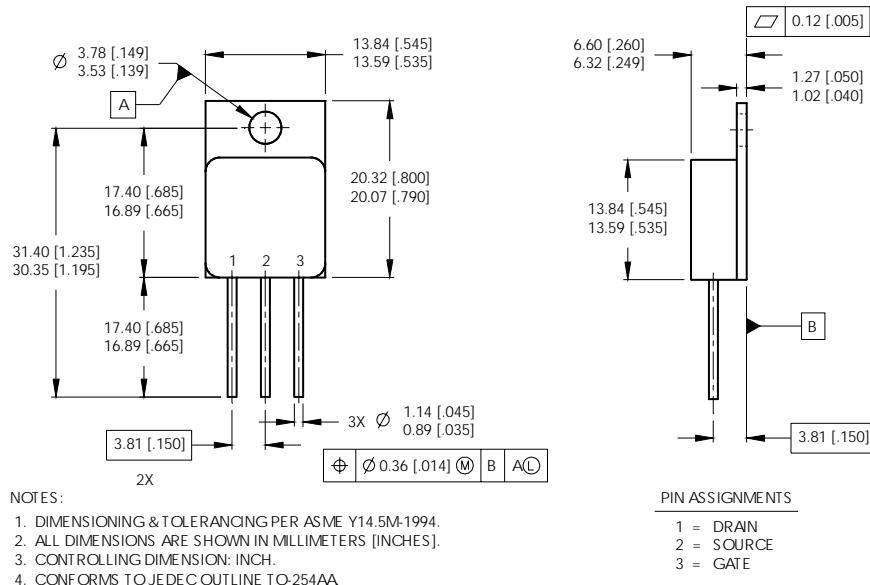


Fig. 10 - Reverse Recovery Waveform and Definitions

Case Outline and Dimensions — TO-254AA



IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

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Data and specifications subject to change without notice. 03/01